

Application for
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for

SEMICONDUCTOR DEVICE AND DATA PROCESSING SYSTEM

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- 1 -

SEMICONDUCTOR DEVICE AND DATA PROCESSING SYSTEM

BACKGROUND OF THE INVENTION

The present invention relates generally to a semiconductor device and a data processing system, and more particularly to technologies which are effectively
5 applied to a semiconductor device fabricated by laminating, for example, two semiconductor chips and encapsulating them with a single resin encapsulant, and to settings of identification data in a data processing system using the semiconductor device.

10 As one type of semiconductor device, a semiconductor device called MCP (Multi Chip Package) is known. MCP semiconductor devices having a variety of structures have been developed and manufactured, where the most pervasive one is an MCP semiconductor device
15 which comprises two semiconductor chips that are laminated and incorporated in a single package. For example, JP-A-2-5455 (known reference 1) discloses an MCP semiconductor device which comprises a microcomputer chip having a built-in processor unit
20 operated in accordance with a program, and an EEPROM (Electrically Erasable Programmable Read Only Memory) chip having a built-in non-volatile storage unit as a memory chip laminated on the microcomputer chip. The two chips are encapsulated by a single resin
25 encapsulant to complete the MCP semiconductor device.

JP-A-5-343609 discloses an MCP semiconductor

device which comprises a CMOS (Complementary MOS) chip having built-in circuits mainly composed of MOSFETs (Metal Oxide Semiconductor Field Effect Transistor), and a bipolar chip having built-in circuits mainly composed of bipolar transistors. The two chips are encapsulated by a single resin encapsulant to complete the MCP semiconductor device.

SUMMARY OF THE INVENTION

It is an object of the present invention to provide a semiconductor device and a data processing system which offer a high level of usability.

It is an another object of the present invention to provide a semiconductor device and a data processing system in which a device address can be set with flexibility while ensuring a high reliability.

The above and other objects and novel features of the present invention will become apparent from the description of this specification and the accompanying drawings.

There has been an increasingly high demand for a semiconductor device which has a microcomputer chip and an EEPROM chip incorporated in a single package. The present inventors found the following challenges prior to the development of a semiconductor device which is fabricated by laminating an EEPROM chip on a microcomputer chip, and encapsulating the two chips with a single resin encapsulant.

In a microcomputer system, device identification data (device address) is set for each peripheral circuit such as a memory circuit. In the most convenient way, the device address may be set, for example, by connecting an external terminal (address pin) to a power supply voltage VCC or a ground potential VSS of the circuits on a circuit board, on which the circuits are mounted, to set a binary signal which may take a high level and a low level. However, in the MCP semiconductor device, since the address pin is connected to VCC or VSS at the time the chips are encapsulated by a single resin encapsulant, the identification data is fixed. The identification data thus fixed would cause difficulties and inconvenience in manufacturing and handling the MCP semiconductor device, e.g., manufacturing a plurality of different types of semiconductor devices by setting a plurality of different identification data in semiconductor devices having the same functions such that the semiconductor devices can be adapted to a variety of data processing systems, managing the custody of the semiconductor devices by the identification data, and mounting a semiconductor device having a correct device address in an assembling process.

The following outlines a representative aspect of the invention disclosed in the present application. A semiconductor device includes an internal circuit for performing a circuit operation

corresponding to a signal inputted or outputted through
an input/output interface circuit adapted to a serial
bus, a non-volatile storage circuit for storing
identification data, a comparator circuit for comparing
5 internal identification data stored in the non-volatile
storage circuit with external identification data
included in an input signal supplied through the serial
bus, and a control circuit responsive to a match
detecting signal from the comparator circuit to perform
10 a circuit operation corresponding to an input signal
subsequently supplied through the serial bus to change
the internal identification data in the non-volatile
storage circuit.

The following outlines another representative
15 aspect of the invention disclosed in the present
application. A semiconductor device includes an
internal circuit for performing a circuit operation
corresponding to a signal inputted or outputted through
an input/output interface circuit adapted to a serial
20 bus, and a non-volatile storage circuit for storing
identification data, wherein the internal circuit is
permitted to perform an operation for changing the
identification data by an input signal supplied through
the serial bus when the internal state of the internal
25 circuit transitions to a first state.

The following outlines a further representa-
tive aspect of the invention disclosed in the present
application. A data processing system includes a

plurality of semiconductor devices each having an internal circuit for performing a circuit operation corresponding to a signal inputted or outputted through an input/output interface circuit adapted to the serial bus, and a non-volatile storage circuit for storing identification data, wherein in each of the semiconductor devices, the identification data of each semiconductor device can be changed by an input signal supplied through the serial bus when the internal state of the internal circuit transitions to a first state.

The following outlines a further representative aspect of the invention disclosed in the present application. A semiconductor device includes an internal circuit for performing a circuit operation corresponding to a signal inputted or outputted through an input/output interface circuit adapted to a serial bus, a non-volatile storage circuit for storing identification data, a comparator circuit for comparing internal identification data stored in the non-volatile storage circuit with external identification data included in an input signal supplied through the serial bus, and a control circuit responsive to a match detecting signal from the comparator circuit to perform a circuit operation corresponding to an input signal subsequently supplied through the serial bus to change the internal identification data in the non-volatile storage circuit. Thus, the semiconductor device provides high usability and flexibility in setting a

device address.

A semiconductor device includes an internal circuit for performing a circuit operation corresponding to a signal inputted or outputted through an input/output interface circuit adapted to a serial bus, and a non-volatile storage circuit for storing identification data, wherein the internal circuit is permitted to perform an operation for changing the identification data by an input signal supplied through the serial bus when the internal state of the internal circuit transitions to a first state. Thus, the semiconductor device provides high usability and flexibility in setting a device address.

A data processing system includes a plurality of semiconductor devices each having an internal circuit for performing a circuit operation corresponding to a signal inputted or outputted through an input/output interface circuit adapted to the serial bus, and a non-volatile storage circuit for storing identification data, wherein in each of the semiconductor devices, the identification data of each semiconductor device can be changed by an input signal supplied through the serial bus when the internal state of the internal circuit transitions to a first state to set a device address in the non-volatile storage circuit. Consequently, the data processing system provides effective utilization of a mounting space on a board which underlies the system, or a reduction in

size of the board, as well as flexible adaptability in modification, expansion and the like of the system.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a block diagram generally
5 illustrating an embodiment of a semiconductor device according to the present invention;

Fig. 2 is a block diagram generally
illustrating an embodiment of a data processing system
using semiconductor devices according to the present
10 invention;

Fig. 3 is a block diagram illustrating the
configuration of an embodiment of an IIC bus interface
used in the semiconductor device according to the
present invention;

Fig. 4 is a block diagram illustrating the
15 configuration of a serial EEPROM according to the present invention for explaining the operation of the serial EEPROM;

Fig. 5 shows a memory map and a flow diagram
20 for explaining an exemplary address setting operation for the serial EEPROM according to the present invention;

Fig. 6 is a diagram illustrating the
configuration of an embodiment of a data processing
25 system according to the present invention;

Fig. 7 is a diagram illustrating the
configuration of another embodiment of the data

processing system according to the present invention;

Fig. 8 is a timing diagram for explaining a communication protocol in an IIC bus interface;

Fig. 9 is a block diagram generally
5 illustrating an embodiment of a serial EEPROM according to the present invention;

Fig. 10 is a block diagram generally illustrating another embodiment of the serial EEPROM according to the present invention;

10 Fig. 11 includes a top plan view and a side view illustrating an embodiment of a data processing system according to the present invention;

Fig. 12 is a block diagram illustrating an embodiment of each of semiconductor chips which
15 corresponds to a peripheral circuit that forms part of the data processing system of Fig. 11;

Fig. 13 is a cross-sectional view generally illustrating an embodiment of a non-volatile memory device used in the present invention;

20 Fig. 14 is a diagrammatic plan view illustrating an embodiment of a semiconductor device according to the present invention;

Fig. 15 is a diagrammatic cross-sectional view taken substantially along an a-a section line in
25 Fig. 14;

Fig. 16 is a block diagram illustrating an embodiment of a data processing system according to the present invention;

Fig. 17 is a timing diagram for explaining an exemplary operation of a serial EEPROM according to the present invention;

Fig. 18 is a timing diagram for explaining
5 another exemplary operation of a serial EEPROM according to the present invention; and

Fig. 19 is a timing diagram for explaining a further exemplary operation of a serial EEPROM according to the present invention.

10 DESCRIPTION OF THE EMBODIMENTS

Fig. 1 is a block diagram generally illustrating an embodiment of a semiconductor device according to the present invention. The device of this embodiment is mounted in a system which has a common
15 bus. Stated another way, the semiconductor device is designed to have an input/output interface circuit which is adapted to the common bus. This embodiment employs a strategy of storing a device address assigned to the semiconductor device in a non-volatile memory
20 contained therein, so that the device address of the semiconductor device can be set through software. Though not particularly limited, the common bus is assumed herein to be a serial bus such as IIC bus, where the IIC (I²C) is a trademark of Philips.

25 The device address stored in the non-volatile memory is transferred to a register. A device address comparator circuit compares the device address held in

the register with a device address inputted through the common bus to form a control signal for instructing the semiconductor device to start operating when a match is found between the two device addresses.

5 Though not particularly limited, the non-volatile memory may be an electrically writable and erasable non-volatile memory, the contents of which can be rewritten. With this rewriting operation, the device address can be set again even after the
10 semiconductor device is mounted on a printed board which forms part of a system.

Fig. 2 is a block diagram generally illustrating an embodiment of a data processing system which uses semiconductor devices according to the
15 present invention. As illustratively shown, in this embodiment, the data processing system is composed of at least two boards C, each of which have two semiconductor devices (Device A, Device B) or (Device M, Device N) mounted thereon. When a plurality of
20 semiconductor devices (Devices A through N) are mounted on a single data processing system in this manner, the respective semiconductor devices must be assigned different device addresses from one another.

In this embodiment, each of the semiconductor
25 devices contains a non-volatile memory, as illustrated in the embodiment of Fig. 1, in which the device address is set through software in accordance with an approach, later described, while the respective

semiconductor devices are mounted in the system. This strategy can reduce the number of external terminals of each semiconductor device assigned for the device address, as well as facilitate the manufacturing, custody management, shipment and system assembly because of completely eliminated requirements for consideration on the device addresses corresponding to the respective semiconductor devices mounted in a particular system upon manufacturing, custody management, shipment and assembly of the semiconductor devices.

With the foregoing configuration which enables the device address to be set through software, boards which form part of a data processing system can be standardized as the boards C. Specifically, as compared with a semiconductor device provided with a device address setting pin that is connected to a power supply voltage VCC or to a ground line VSS of a circuit on a board, on which the semiconductor device is mounted, a plurality of circuit boards having different wiring patterns need not be formed corresponding to individual device addresses. The standardized circuit boards C can eliminate such a wiring pattern, thereby resulting in effective utilization or reduction in size of the board space.

Fig. 3 illustrates the configuration of an embodiment of the IIC bus interface which may be used in the semiconductor device according to the present

invention. Though not particularly limited, this embodiment is intended for use with an IIC bus interface EEPROM (Electrically Erasable and Programmable Read Only Memory, hereinafter called the "serial
5 EEPROM").

In the IIC bus interface, the first byte of a communication subsequent to a start condition consists of four bits allocated to a device code; three bits to a device address; and one bit to a R/W bit indicative
10 of read or write. The device code is fixed by the type of particular semiconductor device, and assigned a 4-bit number such as "1010" for an EEPROM as in this embodiment. Different device codes from the above are assigned to other devices such as an A/D converter, an
15 LED driver, and the like, respectively.

Within an input signal supplied through the IIC bus interface, the four bits corresponding to the device code is inputted to a device code comparator circuit which compares the inputted device code with
20 the fixed device code assigned to the semiconductor device. The fixed device code is fixedly set in the semiconductor device by wiring or the like when it was manufactured. The device code comparator circuit compares the fixedly set device code with the inputted
25 device code, and forms a device code matching signal when a match is found between the two device codes.

Within the input signal supplied through the IIC bus interface, the three bits corresponding to the

device address is inputted to a device address
comparator circuit which compares the inputted device
address with a device address set in the non-volatile
memory. The device address in the non-volatile memory
5 has been set at an arbitrary address by a writing
operation or a rewriting operation, later described.
The device address comparator circuit compares the
device address set in the non-volatile memory with the
inputted device address to form a device address
10 matching signal when a match is found between the two
device addresses.

The semiconductor device adapted to the IIC
bus interface (IIC I/F Device) in this embodiment
starts a read or a write operation in response to the
15 signal R/W when the device code matching signal and
device address match signal are both formed. The read
or write operation, details of which will be later
described, may be outlined as follows. An internal
address is specified by an address signal included in
20 an input signal which is inputted subsequent to the
input signal including the device code, device address
and R/W, and the semiconductor device fetches and
writes write data included in a subsequently incoming
input signal when a write operation is instructed, and
25 outputs read data to the IIC bus when a read operation
is instructed.

Fig. 4 illustrates the configuration of the
serial EEPROM according to the present invention for

explaining an exemplary operation of the serial EEPROM.
In the serial EEPROM of the illustrated embodiment, a
device address is set in a built-in device address
memory (non-volatile memory). A power-on reset circuit
5 generates a power-on reset signal when a power supply
voltage VCC reaches a predetermined level. This power-
on reset signal is sent to a load control logic circuit
which supplies the device address memory with a device
address load signal in response to the power-on reset
10 signal inputted thereto.

The device address memory, responsive to the
device address load signal supplied thereto, reads the
stored device address which is transferred to a device
address register. Consequently, the device address
15 register holds the device address which is stored in
the device address memory.

Thus, when an input signal such as that shown
in Fig. 3 is supplied to the serial EEPROM through the
IIC bus, the device address comparator circuit compares
20 the device address loaded into the device address
register in response to the power-on reset signal with
the inputted device address, rather than accessing the
device address memory to retrieve the device address
stored therein each time the input signal is supplied.
25 The device address matching signal formed in the device
address comparator circuit is sent to a Read/Write
control circuit which forms a Read/Write operation
start signal.

Though omitted in Fig. 4, the EEPROM includes an address input circuit, an address select circuit, a memory array, and the like, all of which is controlled by a control circuit that includes the Read/Write control circuit and the like.

Fig. 5 shows a memory map and a flow diagram for explaining an exemplary address setting operation for the serial EEPROM according to the present invention. In the memory map for the serial EEPROM, addresses from H'0000 to H'FFFF are allocated, wherein an area from H'0000 to H'01FF is used as a memory area of the EEPROM for storing data and programs. In the remaining address space from H'0200 to H'FFFF, a portion is allocated for addresses of a device address memory and a key register, while the remainder is reserved.

On the assumption that the serial EEPROM has the foregoing address space in the memory map, a device address rewriting flow (procedure) is executed in the following manner. At step (1) in Fig. 5, the key register is accessed. In other words, an input signal as shown in Fig. 3 is supplied through the IIC bus. The serial EEPROM is provided with a device code and a device address, and is instructed to perform a write operation. On the promise of this operation, a preliminary device address has been written into a device address memory comprised of the non-volatile memory in the serial EEPROM. This preliminary device

address is also used for memory accesses for writing and reading in a probe test, a burn-in test after assembly, and the like of the serial EEPROM. In other words, since the device code and device address are
5 essentially inputted for accessing the serial EEPROM of this embodiment, the preliminary device address must have been stored as well for the operation tests and the like.

An address signal, to which the key register
10 is assigned, is inputted using the preliminary device address, and a predetermined key code is written at step (2). The internal control circuit compares the key code written into the key register with the preset key code, and forms a signal for granting an access to
15 the device address memory when a match is found between the two key codes. An address signal, to which the device address memory is assigned, is written at step (3), and a device address different from the preliminary device address is inputted to re-write the
20 preliminary device address at step (4).

By employing the device address re-writing procedure as described above, a device address to be preserved can be prevented from being erroneously re-written by data or a portion of a program written into
25 the device address memory as a result of an erroneously specified address, which inadvertently corresponds to the device address memory, during a normal write operation to the serial EEPROM. In other words, since

an access to the key address register and the matching of the key codes must be accomplished before writing data which is to be re-written with the address of the device address memory, an access to the device address memory is not granted only by erroneously specifying its address in a normal write operation of the serial EEPROM. In this manner, the device address can be arbitrarily set or re-written while ensuring a high reliability.

Fig. 6 illustrates the configuration of an embodiment of a data processing system according to the present invention. The data processing system of this embodiment is composed of two semiconductor devices mounted on a single board which has an IIC bus. The semiconductor devices may be a microcomputer (one-chip microcomputer) which contains an IIC interface, and a serial EEPROM, respectively. The device address of the serial EEPROM is set to a preliminary address n .

When the two semiconductor devices are mounted on the board, the device address n is set in a built-in device address memory of the serial EEPROM, such that the address need not be set on the board. For this reason, the device does not require wires and the like for setting the device address corresponding to a particular semiconductor device mounted thereon, so that the board can be standardized (made common) under the condition that the board is mounted with semiconductor devices to which the present invention is

applied. In addition, the region on the board, from which the wires and the like can be removed, may be allocated for mounting other electronic parts, or cut away to reduce the size of the board. When a data
5 processing system is configured only of two components, i.e., a microcomputer and a serial EEPROM as in this embodiment, the preliminary device address n set for the serial EEPROM can be used as it is.

Fig. 7 illustrates another embodiment of the
10 data processing system according to the present invention. The data processing system of this embodiment is composed of a combination of two boards each having an IIC bus, as illustrated in the embodiment of Fig. 6. Specifically, two boards, each
15 of which has a microcomputer and a serial EEPROM mounted thereon, are interconnected through their respective IIC buses to configure a multi-CPU based data processing system. In such a data processing system, a device address in the serial EEPROM mounted
20 on one board is maintained to be n , while a device address in the serial EEPROM mounted on the other board is re-written from a preliminary address n to m . Since the device address can be changed on-board for the serial EEPROM in this manner, the change of the device
25 address can be applied when the system is extended.

Fig. 8 shows a timing diagram for explaining a communication protocol for use with the IIC bus interface. Fig. 8, which shows a write operation and a

read operation, is provided for explaining the operation viewed from the master side (for example, on the microcomputer side).

The IIC bus interface employs a pair of
5 signal lines for a serial clock (SCL) and a serial input/output (SDA). The serial clock (SCL) is a clock for setting a timing for inputting/outputting serial data. Specifically, data is fetched at a rising edge of the clock, and data is outputted at a falling edge
10 of the clock. It should be noted that the serial clock (SCL) is omitted in Fig. 8.

A pull-up resistor is connected to a serial input/output terminal on the semiconductor device because an output circuit is in an open-drain
15 configuration. Though not particularly limited, the serial EEPROM may be provided with a write protect terminal, such that the write protect terminal, when set to high level, prohibits re-writing of the entire memory array. Therefore, the write protect terminal is
20 set to low level for re-writing the memory array. The write protect terminal is not connected to the serial bus but connected to a dedicated signal line. A read operation can be performed for the entire memory array irrespective of the level of the write protect
25 terminal.

The communication protocol (for a write operation) is explained below. A start condition START is set by changing serial data (SDA) from high level to

low level when the serial clock (SCL) is at high level. After setting START, an 8-bit device address word is routed in synchronism with the serial clock (SCL). The device address word consists of a 4-bit device code, a 3-bit device address, and a 1-bit R/W signal. The R/W signal is set to "0" for a write operation (R/W=0).

In the IIC bus interface, address data as well as read and write data are transmitted/received in units of eight bits, just like the device address word.

10 An acknowledge signal ACK is a signal indicating that the 8-bit data has been normally received. The reception side outputs a logical "0" (low level) at the ninth serial clock (SCL). Specifically, as the 8-bit device address word is transmitted from the master
15 side, the serial EEPROM, on the slave side, transfers the ACK signal set at "0" (ACK=0) at the ninth clock, which is then received on the master side.

Upon receipt of the ACK signal, the master transmits upper eight bits of a memory address (a15 -
20 a8). Then, upon receipt of the ACK signal corresponding thereto, the master transmits lower eight bits of the memory address (a7 - a0). Upon receipt of the ACK signal corresponding to the lower memory address bits (a7 - a0), the master subsequently
25 transmits write data (D7 - D0). Upon receipt of the ACK signal corresponding to the write data (D7 - D0), the master transmits a stop condition STOP. The serial EEPROM on the slave side writes the write data after

5 The write operation into the serial EEPROM
can be applied as it is to the aforementioned step (1)
where the key register is accessed, and step (2) where
a key code is written in the aforementioned Fig. 5.
Specifically, a device address indicated by a device
10 address word specifies the preliminary address (address
before re-writing), and a memory address specifies the
address of the key register (8x2) instead of an address
in the memory area. Then, the key code may be inputted
as write data. Subsequently, as the address of the
15 device address memory (8x2) is inputted, a device
address to be re-written is inputted as write data.
Afterward, the master receives the ACK signal from the
serial EEPROM and transmits the stop condition STOP.
In the serial EEPROM, the new device address is written
20 into the device address memory after it is erased.

In the foregoing state remaining unchanged, although a new device address will be written into the device address memory, the previous device address is still stored in the device address register, so that the new device address written into the device address memory is loaded into the device address register by once powering off and again powering on the serial EEPROM, or by inputting a special signal, as described

later.

The communication protocol (for a read operation) is explained below. As is the case with the write operation, a start condition (START) is inputted, and an 8-bit device address word is routed in synchronism with the serial clock (SCL). The device address word consists of a 4-bit device code, a 3-bit device address, and a 1-bit R/W signal. In this event, the R/W signal is set to "0" (low level). Upon receipt of the ACK signal corresponding to the device address word, the master transmits upper eight bits of a memory address (a15 - a8). Upon receipt of the ACK signal corresponding to the upper half of the memory address, the master transmits lower eight bits of the memory address (a7 - a0). Up to this time, a dummy write operation is performed in spite of the read operation. In other words, the dummy write operation is utilized for inputting the address for the read operation.

The serial EEPROM has an internal address counter which increments a lastly accessed address (N) in the preceding read operation or write operation by one and holds the resulting address (N+1). Thus, a read operation can be performed using this address (N+1). For this reason, an address signal need not be inputted each time a read operation is performed. The aforementioned dummy write operation is used for setting a new address irrespective of the preceding access.

The start condition (START) is again inputted, and a device address word is inputted. Specifically, as the device code and device address are inputted and the R/W signal is set to logical "1" in a manner similar to the write operation, read data D7 - D0 are outputted from the serial EEPROM after the ACK signal is received. In other words, the read data is outputted from the address (N+1) specified by the dummy write operation. The acknowledge signal set at "1"

10 (ACK=1) and stop condition STOP are inputted in this order (the bus may be opened instead of inputting the ACK signal) after outputting the read data, followed by termination of the read operation with the serial EEPROM.

15 For setting the system in a mode in which data is continuously read, the master sets the ACK signal to logical "0," causing the serial EEPROM to send data from the address (N+2) which is incremented by one from the preceding address. When the end address in the serial EEPROM is reached, the address rolls over to the zero address, thereby enabling continuous reading of sequential data. For terminating such a continuous data read operation, the ACK signal set at "1" (ACK=1) and stop condition STOP are inputted
20 in this order (the bus may be opened instead of inputting the ACK signal) in the foregoing manner, followed by termination of the reading operation with the serial EEPROM.

Fig. 9 is a block diagram generally illustrating an embodiment of the serial EEPROM according to the present invention. A device address memory c. is implemented by a non-volatile memory as mentioned above, in which "000" has been stored as a preliminary device address during the manufacturing. As the serial EEPROM is powered on, a power-on reset circuit a. is monitoring a power supply voltage VCC, and generates a power-on reset signal k. when the power supply voltage VCC reaches a predetermined level.

A control logic circuit b. generates a load control signal m. in response to the power-on reset signal k.. The load control signal m. is inputted to the device address memory c. to instruct a read operation. A device address n. (000) read from the device address memory c. is transferred to a device address register d.. Consequently, the device address register d. holds the device address n., and sends the held device address p. to a device address comparator circuit e.. With the foregoing operation, the device address is set corresponding to the device address n. stored in the device address memory c.. In this state, an access can be granted to the serial EEPROM as illustrated in Fig. 8.

The operation for rewriting the preliminary device address to an arbitrary address is performed in the following manner. In synchronism with the clock signal SCL on the IIC bus, the start condition and

serial data x.1 corresponding to a device address word
- upper memory address - lower memory address - write
data are inputted to the serial EEPROM through the
serial data bus SDA, in the manner illustrated in Fig.

5 8. The device address comparator circuit e. compares
the device address (000) included in the device address
word with the device address p. (000) held in the
device address register d., and sends a device address
matching signal q. to the control logic circuit b.. It
10 should be noted that the device code assigned to the
serial EEPROM is also compared with an inputted device
code, and the rewrite operation is performed under the
condition that a match is also found between the two
device codes.

15 The control logic circuit b., responsive to
the device address matching signal q. (generated when
the device codes also match), forms a write control
signal r. for instructing a selection of a key register
f. from the upper (H' FF) and lower (H'10) halves of
20 the memory address and a write operation, and outputs a
key code included in the write data to the internal
data bus. In this manner, the key code inputted
through the IIC bus is written into the key register
f..

25 The key code s. written into the key register
f. is sent to a key code monitoring circuit g.. The
key code monitoring circuit g. compares a preset key
code with the key code s. written into the key register

f., and generates a device address memory access grant signal t., when a match is found, and sends the access grant signal t. to the control logic circuit b.

From the IIC bus, in synchronism with the
5 clock signal SCL, the start condition and serial data x.2 corresponding to a device address word - upper memory address - lower memory address - write data are inputted through the serial data bus SDA, in the manner illustrated in Fig. 8.

10 The control logic circuit b., responsive to the device address matching signal q. (generated when the device codes also match), form a write control signal u. for instructing a selection of the device address memory c. from the upper (H'FF) and lower
15 (H'09) halves of the memory address and a write operation, and outputs a new device address (101) included in the write data to the internal data bus. In this manner, the device address inputted through the IIC bus is written into the device address memory c..

20 It should be noted that the preliminary device address "000" is erased prior to the writing as described above. However, the erasing operation may be omitted if the device address "101" can be set by overwriting the preliminary address "000" in the non-
25 volatile memory. In other words, the erasing operation can be eliminated if the device address may be re-written only once, whereas the erasing operation should be performed before the writing if re-writing of the

device address is permitted as many times as required.

In the foregoing state, the new device address "101" has been stored in the device address memory c., while the device address register d. still
5 holds the loaded device address "000." Therefore, even if the re-written address is inputted in this state, the serial EEPROM cannot be accessed. To make the serial EEPROM accessible, it is once powered off and again powered on to load the re-written device address
10 "101" into the device address register d..

When data is subsequently written into the serial EEPROM, the start condition and serial data x.3 corresponding to a device address word - upper memory address - lower memory address - write data are
15 inputted from the IIC bus as the serial data SDA in synchronism with the clock signal SCL in the manner illustrated in Fig. 8.

The control logic circuit b. receives the device address matching signal q. (the device codes
20 also match), selects a memory cell in a memory area indicated in the memory map of Fig. 5 from the upper (H'00) and lower (H'00) memory address to form a write control signal, not shown, and outputs the write data to the internal data bus. Consequently, the data
25 inputted through the IIC bus is written into the memory area. It should be noted that the memory cell at the address H'0000 is erased prior to the writing as described above.

Though not shown, the serial EEPROM may be provided with a reset signal input terminal.

Specifically, the device address memory is read by setting the reset signal input terminal to a

5 predetermined level. Also, other registers and the like may be initialized using the reset signal input terminal. When the serial EEPROM is provided with such a reset signal input terminal, the EEPROM need not be powered off and again powered on each time the device
10 address is changed. Therefore, the provision of the reset signal input terminal can eliminate the power-on reset circuit.

Fig. 10 is a block diagram generally illustrating an embodiment of the serial EEPROM
15 according to the present invention. A device address memory c. is implemented by a non-volatile memory as mentioned above. In this embodiment, a start condition detector circuit a. in a control logic circuit b. is utilized. The start condition detector circuit a. in
20 the control logic circuit b. detects a start condition through a serial data bus SDA in synchronism with a clock signal SCL as mentioned above, in the manner illustrated in Fig. 8, receives a subsequently inputted device address word at an input terminal, generates a
25 load control signal m. to instruct the device address memory c. to perform a read operation, and transfers a stored device address n. to a device address register d.. In this manner, a device address comparator

circuit e. can compare the stored device address n. with a device address which is inputted after the start condition.

In the foregoing configuration, since the
5 device address c. is read each time the start condition is detected, the serial EEPROM need not be once powered off and again powered on each time the device address is changed. In other words, the power-on reset circuit can be eliminated by effectively utilizing the start
10 condition detector circuit a.. Furthermore, the start condition detector circuit a. may be combined with a power-on reset circuit and a reset input signal terminal, and have an additional control register, not shown, which is initialized by a reset signal. When
15 one piece of data in the control register is assigned to indicate whether or not the device address has been transferred, the device address need be transferred only once after resetting the serial EEPROM by updating the data in the control register in response to a
20 transfer of the device address.

Fig. 11 illustrates the configuration of an embodiment of the data processing system according to the present invention. In this embodiment, though not particularly limited, a microcomputer chip and an
25 EEPROM chip may be implemented as a single semiconductor device in a laminate structure. The microcomputer chip and EEPROM chip, integrally encapsulated in the single device, are internally

interconnected through bonding wires corresponding to an IIC bus. The microcomputer chip laminated with the EEPROM chip may be connected to a LCD (liquid crystal display) driver which has an LCD driver chip mounted
5 therein as another peripheral device through an IIC bus formed on a board. Though not particularly limited, the LCD driver may be implemented by CMOS devices.

When there are a plurality of peripheral devices which constitute the data processing system
10 such as the EEPROM and LCD driver, a different device address must be assigned to each of the devices. In this embodiment, each of the EEPROM chip and LCD driver can be assigned a unique device address adapted to the system by storing the device address in its device
15 address memory implemented by a built-in non-volatile memory as mentioned above. When the device address is stored in the built-in non-volatile memory as described above, the semiconductor device does not require address terminals for setting the device address, while
20 the board does not need either wires for communicating high level/low levels for the device address to the address terminals.

Fig. 12 illustrates block diagrams of respective semiconductor chips corresponding to the
25 peripheral circuits which constitute the data processing system of Fig. 11. The EEPROM memory comprises an IIC bus interface circuit (IIC Bus I/F); a logic control circuit (Control logic) as mentioned

above; a device address memory (D.A. Memory); a device
address register (D.A. Register); and a memory matrix
which organizes a memory area. The device address
memory (D.A. Memory) is comprised of memory cells
5 identical to those which constitute the memory matrix.

The LCD driver comprises an IIC bus interface
circuit (IIC Bus I/F); a logic control circuit (Control
logic); a device address memory (D.A. Memory); a device
address register (D.A. Register); and an LCD driver
10 circuit (LCD Driver logic). Since the LCD driver is
comprised of a CMOS circuit, an iFlash memory may be
utilized therefor. This is a non-volatile memory
comprised of a single-layer gate structure that can be
manufactured by the CMOS process, as later described.

15 Fig. 13 is a cross-sectional view generally
illustrating an embodiment of a non-volatile memory
device used in the present invention. A MONOS memory
cell and a FLOTOX memory cell each have a floating gate
for accumulating a data charge, and a control gate in a
20 stacked configuration. For the EEPROM which organizes
a memory area using memory cells in a two-layered gate
structure, the device address memory can be formed
using the process for manufacturing the memory cells as
it is. However, for a semiconductor device formed by
25 the CMOS process as is the case with the LCD driver,
the process for the two-layered gate structure must be
added only for the device address memory because the
gate electrode is formed in a single layer.

On the other hand, the iFlash memory cell is configured by using a gate formed simultaneously with a gate of an N-channel MOSFET as a floating gate, and forming a control gate capacitively coupled with the floating gate of an n-type diffusion layer formed within a semiconductor region. The n-type diffusion layer is formed simultaneously with a source and a drain diffusion layer of the MOSFET. The floating gate, extending horizontally, is formed integrally with a floating gate shown on the right-hand side of Fig. 13, and the floating gate is formed as straddling over the source and drain diffusion layers. In other words, the cross-section of the iFlash memory cell viewed from the left is two-dimensionally formed in a direction shifted by 90° from the cross-section of the same viewed from the right. Thus, the iFlash memory is also called a "non-volatile memory in single-layered gate structure" because of its single-layered gate structure. The iFlash memory cell is described in detail in Japanese Patent Applications Nos. 11-23631, 12-38167, 12-71079, and the like.

By controlling the EEPROM such that a writing or an erasing operation therefor does not result in a depletion mode, a MOSFET for address selection, i.e., a MOSFET having a select gate in Fig. 13 may be omitted from the EEPROM. Thus, other than the MONOS and FLOTOX type ones, non-volatile memory cells constituting the EEPROM may take a variety of implementations.

Fig. 14 illustrates a diagrammatic plan view of an embodiment of a semiconductor device according to the present invention. This embodiment is intended for a QFP (Quad Flatpack Package) semiconductor device.

5 Fig. 14 diagrammatically illustrates the semiconductor device when an upper portion of a resin encapsulant for the semiconductor device is removed. Fig. 15 illustrates a diagrammatic cross-sectional view substantially taken along a section line a-a in Fig. 10 14. As can be seen in Fig. 15, each section line is partially bend such that bonding wires and two semiconductor chips appear in the figure.

A QFP semiconductor device 30A in this embodiment comprises two semiconductor chips (a 15 microcomputer chip 10 and an EEPROM chip 20) laminated one above the other, which are encapsulated by a single resin encapsulant 17.

The microcomputer chip 10 and EEPROM chip 20 are formed in different plane sizes (outer dimensions), 20 and are both two-dimensionally formed in the shape of rectangle. In this embodiment, the microcomputer chip 10 is two-dimensionally formed, for example, in a rectangle of 4.05 [mm] x 4.15 [mm], while the EEPROM chip 20 is two-dimensionally formed, for example, in a 25 rectangle of 1.99 [mm] x 1.23 [mm]. In other words, the EEPROM chip 20 is smaller than the microcomputer chip 10 in plane size. Here, the plane size refers to the size of a surface on which an associated circuit is

formed, so that the EEPROM chip 20 is smaller than the microcomputer chip 10 in the area in which the associated circuit is formed.

The microcomputer chip 10 and EEPROM chip 20
5 comprise, for example, a semiconductor substrate made of single-crystal silicon; a multi-layered wiring layer comprised of a plurality of layers such as an insulating layer and a wiring layer laminated on a circuit forming surface of the semiconductor circuit;
10 and a surface protection film (final protection film) formed to cover the multi-layered wiring layer.

Out of a circuit forming surface (one main surface) 10A and a back surface (the other main surface) of the microcomputer chip 10 opposite to each
15 other, the circuit forming surface 10A is formed with a plurality of bonding pads 11. The plurality of bonding pads 11 are formed on the topmost wiring layer of the multi-layered wiring layer of the microcomputer chip 10. The topmost wiring layer of the multi-layered
20 wiring layer is covered with the surface protection film formed thereon. The surface protection film is formed with bonding openings for exposing the surfaces of the bonding pads 11.

Out of a circuit forming surface (one main
25 surface) 20A and a back surface (the other main surface) of the EEPROM chip 20 opposite to each other, the circuit forming surface 20A is formed with a plurality of bonding pads 21. The plurality of bonding

pads 21 are formed on the topmost wiring layer of the multi-layered wiring layer of the EEPROM chip 20. The topmost wiring layer of the multi-layered wiring layer is covered with the surface protection film formed thereon. The surface protection layer is formed with bonding openings for exposing the surfaces of the bonding pads 21.

Each of the bonding pads 11 of the microcomputer chip 10 and each of the bonding pads 21 of the EEPROM chip 20 are two-dimensionally formed, for example, in a square of 65 [μ m] x 65 [μ m]. The plurality of bonding pads 11 of the microcomputer chip 10 are arranged along the four sides of the microcomputer chip 10. The plurality of bonding pads 21 of the EEPROM chip 20 are likewise arranged along the four sides of the EEPROM chip 20.

The EEPROM chip 20 is mounted on the circuit forming surface 10A of the microcomputer chip 10 with the back surface or the other main surface of the EEPROM chip 20 facing the circuit forming surface 10A of the microcomputer chip 10, and fixedly adhered to the circuit forming surface 10A of the microcomputer chip 10 with an adhesive layer 15 interposed therebetween. In this embodiment, the adhesive layer 15 may be, for example, a polyimide-based adhesive resin film.

The microcomputer chip 10 is fixedly adhered to a die pad 5 with an adhesive layer interposed

therebetween with the back surface thereof facing the die pad 5. The die pad 5 is integrated with four suspending leads 6, such that a supporter 4 is made up of the die pad 5 and four suspending leads 6.

5 The resin encapsulant 17 is two-dimensionally formed in a rectangular shape. In this embodiment, the resin encapsulant 17 is two-dimensionally formed, for example, in a square of 10 [mm] x 10 [mm]. The resin encapsulant 17 is formed of an epoxy-based resin added
10 with a phenol curing agent, silicone rubber, filler and the like for purposes of reducing stress. The resin encapsulant 17 may be formed using a transfer molding method suitable for mass production. The transfer molding method involves using a mold formed with a pot,
15 a runner, an inflow gate, a cavity and the like, and injecting a resin from the pot into the cavity through the runner and inflow gate to form a resin encapsulant.

 Around the microcomputer chip 10, a plurality of leads 2 are arranged along the respective sides of
20 the resin encapsulant 17. Each of the plurality of leads 2 is comprised of an inner lead portion and an outer lead portion integrally formed with the inner lead portion. The inner lead portion of each lead 2 is positioned within the resin encapsulant 17, while the
25 outer lead portion is positioned outside the resin encapsulant 17. In other words, the plurality of leads 2 extend inside and outside the resin encapsulant 17. The outer lead portion of each lead 2 is bent, for

example, in a gull-wing shape which is one of lead shapes for use in the surface mounting.

Bonding pads of the microcomputer chip 10 and EEPROM chip 20 are connected in common to the leads 2 connected to the IIC buses of the chips 10, 20.

Specifically, the leads corresponding to the clock SCL and serial data SDA (represented by the corresponding leads 2 in Fig. 15) of the microcomputer chip 10 and EEPROM chip 20 are connected to associated bonding pads through bonding wires 16, respectively. In other words, the microcomputer chip 10 and EEPROM chip 20 are connected to the IIC bus structure through the two bonding wires 16 within the semiconductor device.

Fig. 16 is a block diagram illustrating an embodiment of a data processing system according to the present invention. A microcomputer chip 10 comprises a processor unit (CPU), a ROM unit (ROM), a RAM unit (RAM), a timer unit (TIM), an A/D converter unit (A/D), a serial communication interface unit (SCI), a data input/output circuit unit (I/O), and the like, all of which are mounted on the same semiconductor substrate. The respective units are interconnected through a data bus 18A and an address bus 18B. The processor unit (CPU) is mainly comprised of a central processing unit, a control circuit, a processing circuit, and the like. The microcomputer chip 10 thus configured is operated, for example, in accordance with a program stored in the ROM unit (ROM).

chip 10 for a write operation and a read operation. The signal transmission paths 25A, 25B are each comprised of the inner lead portions and two bonding wires. In other words, the signal transmission paths 5 25A, 25B are electrically connected to the internal lead portions of the leads 2 respectively through the bonding wires, as illustrated in Fig. 15.

Specifically, the electrical connection of the microcomputer chip 10 to the EEPROM chip 20 is made 10 within the resin encapsulant 17 through the inner lead portions of the lead 2 and the two bonding wires 16. With such a structure, a lead frame developed as suitable for the microcomputer chip 10 can be used, as it is, for any type of microcomputer chip, thereby 15 eliminating the need for newly developing a lead frame adapted to each type of microcomputer chip 10. It is not either necessary to develop each and every type of microcomputer chip which comprises EEPROM bonding pads for electrical connection with the EEPROM chip 20.

20 A serial data signal is outputted from the SDA bonding pad 11A of the microcomputer chip 10, and inputted to the SDA bonding pad 21A of the EEPROM chip 20 through the bonding wire 16, lead 2, and bonding wire 16. A serial clock signal is outputted from the 25 SCL bonding pad 11B of the microcomputer chip 10, and inputted to the SCL bonding pad 21B of the EEPROM chip 20 through the bonding wire 16, lead 2, and bonding wire 16.

In this embodiment, the data processing system comprises two EEPROMs, EEPROM1 and EEPROM2. One of the two EEPROMs, EEPROM1 is attached to the microcomputer chip 10 in a laminate structure, and integrally encapsulated, as illustrated in the aforementioned Fig. 14. On the other hand, the EEPROM2, indicated by hatchings, is used as an external expansion memory. The EEPROM 1 and EEPROM 2 are fabricated on the same semiconductor chip, and the EEPROM 1 is integrated with the microcomputer chip 10 in a laminate structure, while the EEPROM2 is used alone as a single semiconductor device. The expanded EEPROM2 is mounted on a circuit board as illustrated in Fig. 11, and connected to the IIC bus.

In this embodiment, since the EEPROM1 and EEPROM2 are mounted in a single data processing system, different device addresses must be set to them, respectively. For setting different device addresses, the device address memory may be re-written as described above, such that the preliminary device address "000" is left unchanged in one EEPROM, while a different device address such as "101" is substituted for the preliminary device address in the other EEPROM.

Fig. 17 shows a timing diagram for explaining an exemplary operation of the serial EEPROM according to the present invention. This timing diagram corresponds to the embodiment illustrated in Fig. 9. As previously described, the control logic circuit b.

receives the power-on reset signal k. formed by the power-on reset circuit a., selects the device address memory c. in response to a clock signal internal to the device (EEPROM), reads the device address stored therein, and stores the read device address in the device address register d..

In Fig. 17, a period 1 is required for the power supply voltage Vcc to rise to a steady-state voltage, and a timing A indicates a load operation start point, i.e., a power-on reset release point. When a predetermined voltage of the power supply voltage Vcc before it rises to the steady-state voltage, i.e., a power supply fluctuation allowable value is $V_{cc} \pm 10\%$ at timing A, the control logic circuit a. detects that the power supply voltage Vcc has reached a predetermined voltage equal to or lower than its minimum voltage, resets the reset signal previously generated corresponding to the rising edge of the power supply voltage Vcc to generate the power-on reset signal.

Upon receipt of the falling power-on reset signal (the reset is released), the control logic circuit b. selects the device address memory c. in response to the internal clock signal to read the device address stored therein, which is held in the device address register d. This operation of the control logic circuit b. is performed in a period 2 which is called a "load operation period." A timing B

indicates a load operation complete timing, from which a device available period begins.

For example, if an external input/output signal (SDA) is changed from high level to low level in a period 3 with the external clock signal (SCL) on the IIC bus remaining at high level, a start condition input (Start) is set. Subsequently, a device address input period 4 is set for inputting an 8-bit device address word in response to the external clock signal. Specifically, a 4-bit device code and a 3-bit device address are inputted, followed by a period 5 in which the eighth write/read mode bit is set (the device addresses are compared within the serial EEPROM). Then, in a period 6 at the ninth bit, the EEPROM sends the ACK signal set at "0," and within the EEPROM, the device address comparator circuit e. outputs the result of comparison between the inputted and stored device addresses.

When the power-on reset circuit a. is used as in the foregoing embodiment, a voltage having a certain margin is used in consideration of fluctuations in the power supply voltage Vcc for generating the power-on reset signal. For this reason, when the operating voltage of the EEPROM is reduced, the power supply voltage Vcc is further reduced at the time the power-on reset signal is generated. For example, when the power supply voltage Vcc is at a relatively high voltage, for example, approximately 3.3 V, a power-on reset release

voltage may be set at a relatively high voltage such as 2.5 - 2.6 V.

However, when the power supply voltage V_{cc} is at a relatively low voltage of approximately 2.0 - 2.5 V, the power-on reset release voltage will be set at a low voltage such as 1.5 - 1.8 V. When the reset is released to access the device address memory as described above with such a low voltage, a sufficient voltage is not provided for reading the device address from the device address memory, possibly resulting in a malfunction that the correct device address cannot be read. From the foregoing, it is appreciated that the embodiment illustrated in Fig. 10, which has the start condition detector circuit a. built in the control logic circuit b. and reads the device address using an external clock signal, is advantageous from a viewpoint of the prevention of malfunction for a device which operates at a low voltage (2.0 - 2.5 V).

Fig. 18 shows a timing diagram for explaining another exemplary operation of the serial EEPROM according to the present invention. This timing diagram corresponds to the embodiment illustrated in Fig. 10. As previously described, the start condition detector circuit a. is built in the control logic circuit b. such that the device address is read using an external clock signal.

In Fig. 18, a period 1 is required for the power supply voltage V_{cc} to rise to a steady-state

voltage, similar to Fig. 17. A timing b indicates a device available point at which the power supply voltage V_{cc} reaches the steady-state voltage. In this embodiment, the device is made available without an effective device address held in the device address register. Therefore, in a period 3, a start condition input (Start) is set by changing the external input/output signal (SDA) from high level to low level when the external clock signal (SCL) on the IIC bus is at high level.

Subsequently, a device address input period 4 is set in response to the external clock signal for inputting an 8-bit device address word. Specifically, a 4-bit device code and a 3-bit device address are inputted, followed by a period 5 in which the eighth write/read mode bit is set (the device addresses are compared within the serial EEPROM). Then, in a period 6 at the ninth bit, the EEPROM sends the ACK signal set at "0," and within the EEPROM, the device address comparator circuit e. outputs the result of comparison between the inputted and stored device addresses.

As the start condition detector circuit a. provided in the control logic circuit b. detects a start condition inputted in the period 3, the start condition detector circuit a. selects the device address memory c. in response to a signal internal to the device (EEPROM) using the clock signal in a period 2 which is parallel with a device address input

included in the period 4, reads the device address stored therein, and stores the read device address in the device address register d. before the input device address is compared with the stored device address at the eighth bit.

In this embodiment, though not particularly limited, trimming data may be loaded in a period 2' newly provided after the period 6 in which the ACK signal set at "0" is sent. The period 2' is included in a period 7 in which the first address is subsequently inputted. The trimming data, which may be provided for compensating the device for variations introduced within the manufacturing process, is stored in a memory device similar to the device address memory, such that the trimming data is read for compensating associated circuits for variations due to the process.

Though not particularly limited, the EEPROM may contain a power supply circuit which includes a charge pump circuit for forming a high voltage for writing or a high voltage for erasure. Since the writing voltage or erasing voltage is a critical parameter which determines the amount of writing or the amount of erasure of the storage device, the voltage must be highly accurately set. However, since variations in MOSFETs introduced during the manufacturing process thereof make it difficult to set a desired voltage, trimming data for compensating the

MOSFETs for the variations should be stored in a non-volatile memory, such that the trimming data is read, when the EEPROM starts operating, to control the voltage, thereby making it possible to implement stable writing and erasing operations without being affected by the variations in MOSFET devices due to the manufacturing process.

Fig. 19 shows a timing diagram for explaining a further exemplary operation of the serial EEPROM according to the present invention. This timing diagram shows how the control logic circuit b. loads a device address and trimming data in the period 2 and period 2' in the aforementioned Fig. 18.

As a start condition is set by the clock signal SCL and serial data SDA, the start condition detector circuit a. detects the start condition. In the first cycle (device address input period) from the first to ninth clock signals SCL, a word line is selected for the device address at the third clock, and 8-bit data is outputted to a data bus D[7:0] at the fourth clock. Then, a device address SLA [2:0] comprised of 3-bit data within the 8-bit data is stored in the device address register.

Subsequently, in the second cycle (first memory address input period) from the first to ninth clock signals SCL, a word line is likewise selected for a trimming memory at the third clock, and 8-bit data is outputted to the data bus D[7:0] at the fourth clock.

Then, trimming data M[4:0] comprised of 5-bit data within the 8-bit data is stored in a trimming register.

As described above, the following benefits can be provided according to the foregoing embodiments.

5 (1) A semiconductor device having an internal circuit which performs a circuit operation corresponding to a signal inputted/outputted through an input/output interface circuit adapted to a serial bus is provided with a non-volatile storage circuit for
10 storing identification data. Internal identification data stored in the non-volatile storage circuit is compared with external identification data included in an input signal supplied through the serial bus by a comparator circuit. A control circuit, responsive to a
15 match detecting signal from the comparator circuit, performs a circuit operation corresponding to a subsequently supplied input signal through the serial bus. The control circuit is capable of changing the internal identification data stored in the non-volatile
20 storage circuit so that a device address can be set in the semiconductor device, thereby making the semiconductor device highly usable and flexible.

 (2) Under the condition that the identification data stored in the non-volatile storage circuit
25 transitions to a predetermined state, an internal identification signal is read and transferred to a predetermined storage circuit, so that the device address can be consistently and rapidly determined.

(3) The semiconductor device further comprises a power supply voltage detector circuit for receiving a power supply voltage to detect that the power supply voltage reaches a first level to create
5 the predetermined state, so that the device address can be consistently and rapidly determined.

(4) The semiconductor device further comprises a reset signal input terminal, wherein the predetermined state is set when a predetermined signal
10 is inputted to the reset signal input terminal, thereby making it possible to eliminate a tedious operation of once shutting off and again turning on the power supply voltage for loading a re-written device address into the device address register as well as to simplify the
15 circuit configuration because a dedicated supply voltage detector circuit is not required.

(5) The circuit configuration in the semiconductor device can be simplified by setting the predetermined state by a predetermined input signal
20 which is first supplied through the serial bus after the power is turned on.

(6) As assigned circuit operations, the control circuit performs an operation for rewriting identification data in the non-volatile storage circuit
25 in response to the input signal, and an operation directed to the internal circuit in response to the input signal, so that the serial bus standard can be utilized as it is to set a device address.

(7) The semiconductor device further comprises a second input/output interface circuit adapted to the serial bus, and a signal processing circuit provided through the second input/output interface circuit. The second input/output interface circuit and signal processing circuit are mounted in a first semiconductor chip. The first input/output interface circuit, internal circuit, non-volatile storage circuit, comparator circuit, and control circuit are mounted in a second semiconductor chip. On the main surface of the first semiconductor chip, the second semiconductor chip is integrally encapsulated in a laminate structure, so that the semiconductor device is low in cost, small in size and high in performance.

(8) The serial bus is configured to connect the two semiconductor chips through first bonding wires for connecting bonding pads corresponding to the second input/output interface circuit in the first semiconductor chip to associated leads, and second bonding wires for connecting bonding pads corresponding to the first input/output interface circuit in the second semiconductor chip to associated leads. With this serial bus, the two semiconductor chips can be combined in a flexible and simple manner.

(9) The first semiconductor chip includes a processor unit, and a ROM for storing a signal processing procedure performed by the processor unit, while the second semiconductor chip includes a memory

circuit which is allocated an address space different from an address space allocated to the non-volatile storage circuit for storing the identification data, thereby providing the small and high performance
5 semiconductor device which can be flexibly adapted to any data processing system.

(10) The memory circuit is comprised of memory cells in the same structure as the non-volatile storage circuit for storing the identification data,
10 thereby making it possible to reasonably manufacture a single semiconductor device having two circuits formed through difference semiconductor processes.

(11) The internal circuit comprises a CMOS circuit, and the non-volatile storage circuit for
15 storing the identification data is comprised of non-volatile memory cells in a single-layered gate structure formed by a manufacturing process used for manufacturing the CMOS circuit, thereby making it possible to streamline the manufacturing process.

(12) The internal identification data
20 includes first internal identification data and second internal identification data, and the comparator circuit and control circuit compare third external identification data included in a first input signal
25 supplied through the serial bus with the first internal identification data stored in the non-volatile storage circuit, and compare fourth external identification data included in the first input signal with second

internal identification data stored in the non-volatile storage circuit when the first internal identification data matches the third external identification data, such that the first internal identification data can be
5 changed by a second input signal supplied subsequently to the first input signal through the serial bus under the condition that the second internal identification data matches the fourth external identification data, thereby making it possible to change the device address
10 with a high reliability.

(13) A semiconductor device having an internal circuit for performing a circuit operation corresponding to a signal inputted or outputted through an input/output interface circuit adapted to a serial
15 bus is provided with a non-volatile storage circuit for storing identification data, wherein the circuit operation performed by the internal circuit includes an operation for changing the identification data by an input signal supplied through the serial bus when an
20 internal state transitions to a first state. Thus, the resulting semiconductor device is highly usable, and flexible in setting a device address.

(14) The internal identification data includes first internal identification data and second
25 internal identification data, and the internal circuit compares third external identification data included in a first input signal supplied through the serial bus with first internal identification data stored in the

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non-volatile storage circuit, and compares fourth
external identification data included in the first
input signal with second internal identification data
stored in the non-volatile storage circuit when the
5 first internal identification data matches the third
external identification data under the condition that
the second internal identification data matches the
fourth external identification data, and performs an
operation for changing the first internal identific-
10 ation data by a second input signal supplied subsequent
to the first input signal through the serial bus,
thereby making it possible to change the device address
with a high reliability.

(15) When the serial bus is implemented by
15 an IIC bus, signals can be communicated through two
signal lines, and the system design is facilitated.

(16) A data processing system is configured
by a plurality of semiconductor devices, each of which
comprises an internal circuit for performing a circuit
20 operation corresponding to a signal inputted or
outputted through an input/output circuit adapted to a
serial bus, and a non-volatile memory for storing
identification data. In each of the semiconductor
devices, when the internal state of the internal
25 circuit transitions to a first state, the identifica-
tion data can be changed by an input signal supplied
through the serial bus to set a device address.
Consequently, the data processing system provides

(17) The identification data of each semiconductor device includes first identification data and second identification data, and the internal circuit of each semiconductor device compares third identification data included in a first input signal supplied through the serial bus with first identification data stored in the non-volatile storage circuit, and compares fourth identification data included in the first input signal with second identification data stored in the non-volatile storage circuit when the first identification data matches the third identification data, such that under the condition that the second identification data matches the fourth identification data, the internal circuit in each semiconductor device sets different identification data in the associated semiconductor device by a second input signal supplied subsequent to the first input signal through the serial bus, thereby making it possible to set the device address with a high reliability.

While the invention made by the present
inventors has been described in a specific manner with

reference to the foregoing embodiments, the present invention is not limited to those embodiments but may be changed in various ways without departing from the spirit and scope of the invention. For example, for
5 the serial bus, other buses such as the CAN bus standard mainly utilized for cars, serial ATA, USB or IEEE1394 for personal computers, and the like may be utilized as well other than the IIC bus.

The device address memory may employ a fuse
10 or the like which is electrically cut off, other than the non-volatile memory as described above. However, since the fuse-based device address memory allows the writing only once, the re-writable non-volatile memory is better in usability. The present invention can be
15 widely utilized in a variety of semiconductor devices which require device addresses, and serial bus-based data processing systems which use a device address to access a peripheral device. For example, an exemplary system having a plurality of devices interconnected
20 through such a serial bus may be a notebook type personal computer in which a plurality of battery units can be connected, wherein the respective battery units are connected to a serial bus such that each of the batteries can be monitored for the power consumption.
25 Another exemplary system may be a car-equipped audio system which allows a driver to make identification between subsequently added devices and previously mounted devices.